

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (PTO-1449)			ATTY. DOCKET NO. <b>43889-951</b>		SERIAL NO. <b>(Divisional of Serial No. 08/965,892)</b> <i>07/610,440</i>		
			APPLICANT <b>Koji ERIGUCHI, et al.</b>				
			FILING DATE <b>July 05, 2000</b>		GROUP <b>2825</b>		
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
<i>CME</i>	4,652,757	3/87	Carver	-	-	-	
<i>CME</i>	4,750,822	6/88	Rosencwaig et al.	-	-	-	
<i>CME</i>	5,260,772	11/93	Pollak et al.	-	-	-	
<i>CME</i>	5,536,936	7/96	Drevillon et al.	-	-	-	
<i>CME</i>	4,211,488	7/80	Kleinknecht	-	-	-	
<i>CME</i>	5,365,334	11/15/94	Botka	-	-	-	
<i>CME</i>	5,379,109	1/3/95	Gaskill et al.	-	-	-	
<i>CME</i>	5,313,044	5/17/94	Massoud et al.	-	-	-	
<i>CME</i>	5,314,831	5/24/94	Hirae et al.	-	-	-	
<i>CME</i>	5,663,657	9/2/97	Lagowski et al.	-	-	-	
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<i>CME</i>	0655620	11/29/94	Europe	-	-		
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
<i>CME</i>	"Supervisory Run-To-Run Control of Polysilicon Gate Etch Using In Situ Ellipsometry", by Butlers et al., IEEE Transaction on Semiconductor Manufacturing, Vol. 7, No. 2, May 1, 1995, pp. 193-201.						
<i>CME</i>	"Measurement of Damage Profile in Semiconductors: A Sensitive Optical Technique", by Shwe et al., Applied Physics Letters, Vol. 62, No. 5, February 1, 1993, pp. 516-518.						
EXAMINER <i>C. Luskast</i>				DATE CONSIDERED <i>7-31-02</i>			